

Claim 7, line 7, delete "of" (second occurrence) insert  
--at--.

Claim 11, line 8, delete "of" (first occurrence) insert  
--at--;

line 13, before "a" insert --setting--;

line 14, delete "is set"; same line 14, delete "and"  
insert --, whereby--.

Claim 14, line 3, delete "?m" insert -- $\mu$ m--.

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15. (amended) A method according to claim 14, wherein  
A' the electrostatic [B] chucking of the sample is [that of]  
effected by a dipole type electrostatic chuck.

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18. (amended) A sample surface treating apparatus  
comprising:

A2 a stage which is provided in a chamber and on which a  
sample to be subjected to a surface treatment is to be placed;  
etching gas supplying means for continuously supplying an  
etching gas for plasma generation into the chamber;  
plasma generating means for generating a high-density  
plasma in the chamber;  
a bias power supply for applying a bias voltage of 100  
kHz or higher to the stage independently of the plasma  
generation; and  
pulse modulating means for modulating the bias power